


REMARKS

By this Preliminary Amendment claims 3 and 4 have been amended to correct minor typographical errors. Also, claims 1-5 have been amended to correct minor paragraph spacing inconsistencies between the limitations. Finally, Applicant has added new claims 24-28 to recite additional protection to which Applicant is entitled.

Submitted concurrently is a *Petition to Withdraw from Issue Under 37 CFR §1.313* and *Request for Continued Examination (RCE)*. Examination on the merits is requested.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 1-5 as follows:

1. A method for manufacturing a semiconductor device comprising the steps of:

forming an interlayer insulator comprising at least upper and lower layers, each comprising different dry etching characteristics;

etching the upper layer of the interlayer insulator using a first mask, wherein the lower layer of the interlayer insulator is used as an etching stopper;[]

forming a second mask to cover a portion of the lower layer of the interlayer insulator, which is exposed by the etching step; and

selectively etching the lower layer of the interlayer insulator using the second mask to form a contact hole.

2. A method for manufacturing a semiconductor device comprising at least one thin film transistor comprising the steps of:

forming a first conductive film on a gate insulating film;

patterning the first conductive film to form a gate electrode;

forming an interlayer insulator comprising at least two layers on the gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole through the interlayer insulator to reach at least one of the source region and the drain region;

forming a second conductive film;

patterning the second conductive film to form a pixel electrode;[]

forming a third conductive film; and

patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with the pixel electrode.

3. (Amended) A method for manufacturing a semiconductor device comprising at least one thin film transistor, comprising the steps of:

forming a first conductive film comprising aluminum on a gate insulating film;

patterning the first conductive film for forming a gate electrode;

forming an interlayer insulator comprising at least two layers on said gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole through [te] the interlayer insulator to reach at least one of the source region and the drain region;

forming a second conductive film;

patterning the second conductive film for forming a pixel electrode;

forming a third conductive film; and

patterning the third conductive film for forming at least one of a source electrode and a drain electrode, which is in electrical contact with said pixel electrode.

4. A method for manufacturing a semiconductor device comprising at least one thin film transistor, comprising the steps of:

forming a first conductive film on a gate insulating film;[]

patterning the first conductive film to form a gate electrode;[]

forming an interlayer insulator comprising at least two layers on said gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole to reach at least one of the source region and the drain region;

forming a second conductive film;
patterning the second conductive film to form a pixel electrode;[]
forming a third conductive film; and
patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with said pixel electrode, wherein the contact hole is formed smaller than the part.

5. A method for manufacturing a semiconductor device comprising at least one thin film transistor comprising the steps of:

forming a first conductive film on a gate insulating film;[]
patterning the first conductive film to form a gate electrode;[]
forming an interlayer insulator on the gate insulating film;
removing a part of the interlayer insulator, the part being located over at least one of a source region and a drain region;
forming a contact hole through the interlayer insulator to reach at least one of the source region and the drain region;
forming a second conductive film;
patterning the second conductive film to form a pixel electrode;[]
forming a third conductive film; and
patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with the pixel electrode.